Hybrid integrated IGBT driver





Patent protection



RoHS

- 600V series IGBT (current ≤600A)
- 1,200V series IGBT (current ≤400A)
- 1,700V series IGBT (current ≤200A)

FEATURES

- Built-in isolated DC-DC power supply; Single power supply drive topology
- High isolation voltage of 3750VAC
- Input signal frequency up to 20kHz
- Built-in fault circuit with a pin for fault feedback
- Drive signal ignored during blocking time, fault circuit reset after blocking time end
- Adjustable controlled time of fault detection circuit
- Adjustable protective soft cut-off time
- SIP package
- EN62368 approval

Applications

Universal inverter

Matched IGBT

- AC servo drive system
- **UPS systems (Uninterruptible Power Supply)**
- Electric welding machine

QP12W08S-37 is an integrated hybrid IGBT driver designed with a built-in isolation DC-DC converter. This device is a fully isolated gate drive circuit consisting of an optimally isolated gate drive amplifier and an isolated DC-DC converter. The gate driver provides a fault protection function based on desaturation detection and fault output.

Selection Guide							
			Output			Maximum	
Certification	Part No.	Input Voltage (VDC)	Output High-level Voltage V _{OH} (VDC)	Output Low-level Voltage Vol (VDC)	Max. Driving Current (A)	capacitive load (uF)	
CE	QP12W08S-37	15	15	-9	±8	5400	

Maximum ratings				
Item	Symbol	Testing Conditions*	Value	Unit
Power Supply Input Voltage	V_D	DC	16	V
Input Impulse High-level Current	$I_{I\!H}$	Between PIN3 and PIN4	25	mA
D O D	I_{gon}	Pulse Width 2us	+8	
Driver Output Peak Current	I_{goff}	Frequency f=20kHz	-8	Α
Fault Output Current	I_{fo}		20	mA
Max. Input Voltage to Fault Detect Pin	V_{R1}	Applied Pin13	50	V

Item		Symbol	Testing Conditions	Min.	Тур.	Max.	Unit
Power Supply	Input Voltage	V_D		14.5	15	15.5	V
	Input Current	I_{in}	V _D = 15V, f = 20kHz, D = 0.5, Q = 0uC		46		mA
			V _D = 15V, f = 20kHz, D = 0.5, Q = 3.0uC		165		
Input Impulse	High-level Voltage	V_I		3.7		5.7	V
	High-level Current	$I_{I\!H}$		10		20	mA

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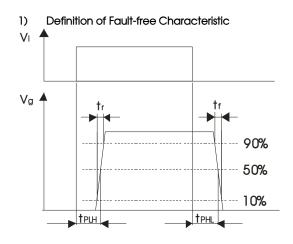
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Output Specifications							
Item		Symbol	Testing Conditions	Min.	Тур.	Max.	Unit
Isolated Power Supply Voltage		V_{CC}	$V_D = 15V, f = 20kHz, D = 0.5$	14.5	16.0	18	
		$V_{\scriptscriptstyle EE}$	$V_D = 15V$, $f = 20kHz$, $D = 0.5$	-7	-8.5	-10	
	High-level Voltage	V_{OH}	V _D = 15V, f = 20kHz, D = 0.5, Q = 3.0uC	14.5	15.0	_	V
	Low-level Voltage	el Voltage V_{OL} $V_D = 15V, f = 20kHz, D = 0.5, Q = 3.0uC$		-7	-9	_	
Drive Output	Rise Time	t_r			0.3	1	0
	Fall Time	t_f			0.3	1	μS
	Total Charge	Q	$V_D = 15V$, $f = 20kHz$, $D = 0.5$	-		3.0	uC

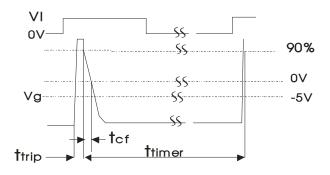
General Specifications							
Item		Symbol	Testing Conditions	Min.	Тур.	Max.	Unit
Operating Frequency		f				20	kHz
Input Impulse	Rise Delay Time	$t_{\scriptscriptstyle PHL}$			0.5	1.2	
and Drive Output	Fall Delay Time	$t_{\it PHL}$		- 1	1	1.2	
Controlled Time of Detect Fault Circuit		t_{trip}	V _D = 15V, fault protection function		3.5	4.0	μS
Fault Soft Turn-off Ti	Fault Soft Turn-off Time		V_D = 15V, fault protection function		4.5	7	
Fault Reset Time	Fault Reset Time		V _D = 15V, fault protection function	1	1.4	2	mS
Fault Threshold Voltage		V_{ocp}	V _D = 15V		9.5		V
Fault Output Termin	Fault Output Terminal Voltage		V _D = 15V, fault protection function		-8.0		V
Insulation Test	Insulation Test		Sine wave 50Hz/60 Hz, 1min,leakage current <1mA			3750	VAC
Operating Tempera	ature	T_{op}		-40		+71	°C
Storage Temperatu	Storage Temperature			-50		+125	
Weight		W			6.7		g
Safety Standard	Safety Standard			EN62368			
Safety Certification	Safety Certification			EN62368			
Safety Class				CLASS III	CLASS III		

Design Reference

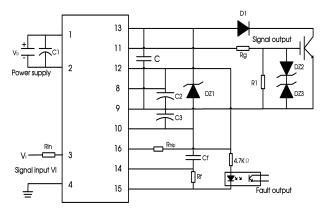
1. Description of Characteristic



2) Definition of Fault Characteristic



2. Typical application



C1	100µF		
C2	100µF		
C3	100µF		
Rtrip	set as required (optional)		
Cf	set as required (optional)		
Rf	set as required (optional)		
Rg	5 Ω		
R1	10k Ω		
DZ1	TVS (30V, 0.5W)		
DZ2, DZ3	TVS (18V, 1W)		
D1	fast recovery diode (trr \leq 0.2 μ s)		

Note:

- 1. For further ripple & noise reduction, connect an additional capacitor each with a value between 1uF and 10uF in parallel with capacitors C2 and C3.
- 2. If the input impulse voltage is too high, the current-limiting resistance can be adjusted to meet the requirements of the input impulse current. A high-speed opto-coupler LED with a $200\,\Omega$ series resistance is connected in between the signal input terminals and the current-limiting resistance can be calculated according to the following formula:

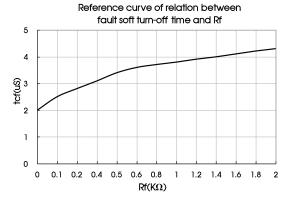
$$R_{\scriptscriptstyle in} = \frac{V_{\scriptscriptstyle I} - 1.7V}{I_{\scriptscriptstyle IH}} - 200\Omega$$

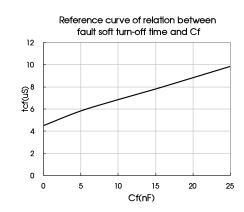
3. For harsh applications in environments with long wires, we recommend adding an additional capacitor C at a distance between 9 feet and 13 feet from the unit as appropriate.

(1) Fault soft turn-off time adjustment:

When a short-circuit or an over-current condition occurs, the driver protection circuit activates and slowly turns off the IGBT. The default turn-off time is 4.5µS, and this turn-off time can be adjusted by connecting an external resistor Rf to reduce the time, or capacitor Cf to increase the time. The adjustment range is 2.5µS to 10µS. The values for protective turn-off time adjustment in the table below are for reference only and must be verified to suite the actual application.

Reference values for Fault soft turn-off time adjustment							
$R_f(K\Omega)$							
_	4.5	_	4.5				
1.5	4.0	1	4.9				
0.5	3.5	3.3	5.3				
0.3	3.0	10	6.5				
0.11	2.5	22	9.3				





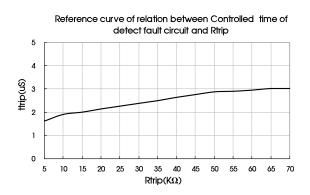
Note: V_D = 15V

(2) Controlled fault detection time adjustment:

When a short circuit or an over current condition occurs, the time from the moment the driver detects a short circuit or an over current condition to when the gate potential drops to 90% of the normal amplitude is called "Controlled Time of Fault Detection". The driver sets the default maximum controlled time for the fault detection circuit and the user can reduce this time, by connecting an external Rtrip resistor. The minimum time that can be adjusted is 1.6µS. The values for adjustment controlled short circuit time detection in the table below are for reference only and must be verified to suite the actual application



Reference values for Controlled fault detection time adjustment					
Rtrip (kΩ)	Ttrip (µS)				
	3.50				
68	3.00				
51	2.80				
30	2.48				
20	2.28				
15	2.0				
10	1.9				
5.1	1.60				



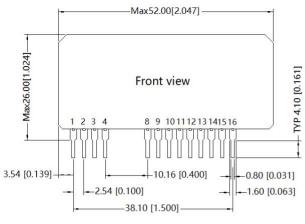
Note: VD=15V.

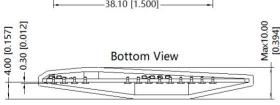
3. For additional information please refer to IGBT Driver application notes on www.mornsun-power.com

Dimensions and Recommended Layout

THIRD ANGLE PROJECTION

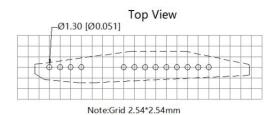






Unit: mm[inch]

Pin section tolerances: ±0.10[±0.004] General tolerances: ±0.50[±0.020]



	Pin-Out						
Pin	Mark	Pin	Mark				
1	Power supply (+)	11	Drive output				
2	Power supply (-)	12	Collector of internal power tube				
3	Drive signal input(+)	13	Detect of short circuit				
4	Drive signal input(-)	14	Adjustment of Soft turn-off time				
8	DC/DC converter output (+)	15	Fault signal output				
9 DC/DC converter output (COM)		16	Adjustment of short-circuit				
10	DC/DC converter output (-)	10	detection time delay				

Notes:

- 1. For additional information on Product Packaging please refer to www.mornsun-power.com. The Packaging bag number: 58230001;
- 2. The built-in isolated DC-DC power supply is for internal driver use only and cannot be used for external connections. We recommend the output filter capacitor value not to exceed 220uF;
- 3. The driver must be wired as short as possible to the IGBT module's gate and emitter terminals (1m max.);
- 4. Twisted pair is recommended for the connection of the driver to the gate and emitter of the IGBT;
- 5. In order to reduce the high peak voltage generated at the collector of the IGBT turn-off, it is recommended to increase the gate resistance appropriately:
- 6. The additional capacitor or resistor should be placed as close as possible to the driver terminals. Do not exceed the recommended maximum values:
- 7. Select electrolytic capacitors for C2 and C3 with a low ESR and placed them as close as possible to the driver terminals;
- 8. Select a fast recovery diode D1 (connected to pin #13) with a peak reverse voltage that is higher than the peak value of the IGBT collector voltage:
- The 30V Zener diode DZ1 is connected between pin #13 and pin #10, protecting the driver from the reverse recovery characteristic of the diode D1 which could generate an excessive voltage on pin #13;
- 4.7KΩ resistance can be connected between pin #13 and pin # 9 if fault detection no required.(D1 and DZ1 is not required in this circuit).
- 11. Unless otherwise specified, parameters in this datasheet were measured under the conditions of Ta=25°C, humidity<75%RH with nominal input voltage and rated output load:
- 12. All index testing methods in this datasheet are based on company corporate standards;
- 13. The above are the performance indicators of the product models listed in this datasheet. Some indicators of non-standard models will exceed the above requirements. For details, please contact our technical staff;
- 14. We can provide product customization service, please contact our technicians directly for specific information;
- 15. Products are related to laws and regulations: see "Features";
- 16. Our products shall be classified according to ISO14001 and related environmental laws and regulations, and shall be handled by qualified units.

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